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DEEP-1001US

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Bin-Shing Chen.

Serial No.: 09/769,576

Group Art Unit: 2811

Filed: January 14, 2001

Examiner: Thien F. Tran

For: Method for Manufacturing Split Gate EEPROM Memory Cell and
Structure Formed Thereby

Mail Stop AF
Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AFTER FINAL AMENDMENT

Sir:

In response to the Final Rejection dated October 13, 2004, please amend the above-captioned patent application as follows:

Amendments in the Claims are reflected in the listing of claims that begins on page 2 of this paper.

Remarks/Arguments begin on page 4 of this paper.

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8

I certify that this document, along with any document referred to as being attached, is being deposited with the U.S. Postal Service as first class mail on January 13, 2005, under 37 C.F.R. §1.8 and is addressed to Mail Stop AF, the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Carla P. Morrissey
Name of person signing document

Carla P. Morrissey
Signature of person signing document